

### **SPECIFICATION AMENDMENTS**

Please insert at the first line --This application is a divisional of U.S. Patent Application Serial No. 10/176,336 filed June 20, 2002--.

Please replace the paragraph on page 4, lines 8-15 to read:

Referring to Figure 4, the spacers 16 may be removed, leaving the exposed germanium implanted regions 17 in the substrate 10. At this point, the P-type source/drain extension implant may be done. In one embodiment, the P-type source/drain extension implant may be Boron 11. As a result of the Boron implant, an implanted region 18 may be formed that overlaps the implanted region ~~16~~ 17 that includes germanium as shown in Figure 5.